



# PJS6415AE

## 20V P-Channel Enhancement Mode MOSFET – ESD Protected

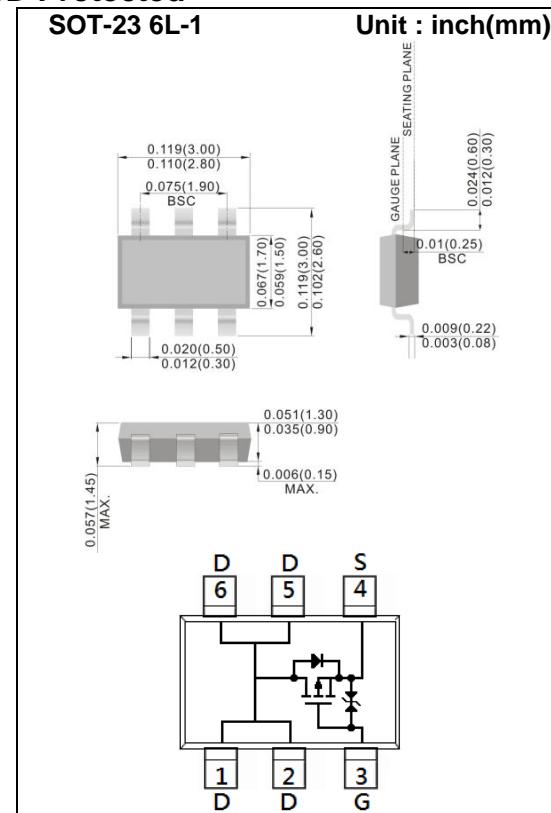
Voltage      **-20 V**      Current      **-4.9A**

### Features

- RDS(ON) , VGS@-10V, ID@-4.9A<60mΩ
- RDS(ON) , VGS@-4.5V, ID@-4.2A<70mΩ
- RDS(ON) , VGS@-2.5V, ID@-3.1A<96mΩ
- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc
- ESD Protected 2KV HBM
- Lead free in comply with EU RoHS 2011/65/EU directives.
- Green molding compound as per IEC61249 Std.  
(Halogen Free)

### Mechanical Data

- Case: SOT-23 6L-1 Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0003 ounces, 0.0084 grams
- Marking: S5E



### Maximum Ratings and Thermal Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS
Drain-Source Voltage	$V_{DS}$	-20	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Continuous Drain Current	$I_D$	-4.9	A
Pulsed Drain Current	$I_{DM}$	-19.6	A
Power Dissipation	$T_a=25^\circ\text{C}$	2	W
	$P_D$	16	mW/°C
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~150	°C
Typical Thermal resistance - Junction to Ambient <sup>(Note 3)</sup>	$R_{\theta JA}$	62.5	°C/W



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**Electrical Characteristics** ( $T_A=25^\circ C$  unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
<b>Static</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-20	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.5	-0.77	-1.2	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-4.9A$	-	50	60	$m\Omega$
		$V_{GS}=-4.5V, I_D=-4.2A$	-	58	70	
		$V_{GS}=-2.5V, I_D=-3.1A$	-	80	96	
		$V_{GS}=-1.8V, I_D=-0.5A$	-	140	180	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-20V, V_{GS}=0V$	-	-0.01	-1	$\mu A$
Gate-Source Leakage Current	$I_{GSS}$	$V_{GS}=\pm 8V, V_{DS}=0V$	-	$\pm 6$	$\pm 10$	$\mu A$
<b>Dynamic</b> <small>(Note 5)</small>						
Total Gate Charge	$Q_g$	$V_{DS}=-10V, I_D=-4.9A,$ $V_{GS}=-4.5V$ <small>(Note 1,2)</small>	-	6.9	-	$nC$
Gate-Source Charge	$Q_{gs}$		-	1.5	-	
Gate-Drain Charge	$Q_{gd}$		-	1.9	-	
Input Capacitance	$C_{iss}$	$V_{DS}=-10V, V_{GS}=0V,$ $f=1.0MHz$	-	602	-	$pF$
Output Capacitance	$C_{oss}$		-	70	-	
Reverse Transfer Capacitance	$C_{rss}$		-	47	-	
Turn-On Delay Time	$td_{(on)}$	$V_{DD}=-10V, I_D=-4.9A,$ $V_{GS}=-4.5V,$ $R_G=3\Omega$ <small>(Note 1,2)</small>	-	8.8	-	$ns$
Turn-On Rise Time	$tr$		-	66	-	
Turn-Off Delay Time	$td_{(off)}$		-	29	-	
Turn-Off Fall Time	$tf$		-	14	-	
<b>Drain-Source Diode</b>						
Maximum Continuous Drain-Source Diode Forward Current	$I_s$	---	-	-	-1.5	A
Diode Forward Voltage	$V_{SD}$	$I_s=-1.0A, V_{GS}=0V$		-0.79	-1.0	V

NOTES :

1. Pulse width $\leq 300\mu s$ , Duty cycle $\leq 2\%$
2. Essentially independent of operating temperature typical characteristics.
3.  $R_{QJA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper
4. The maximum current rating is package limited
5. Guaranteed by design, not subject to production testing



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## TYPICAL CHARACTERISTIC CURVES

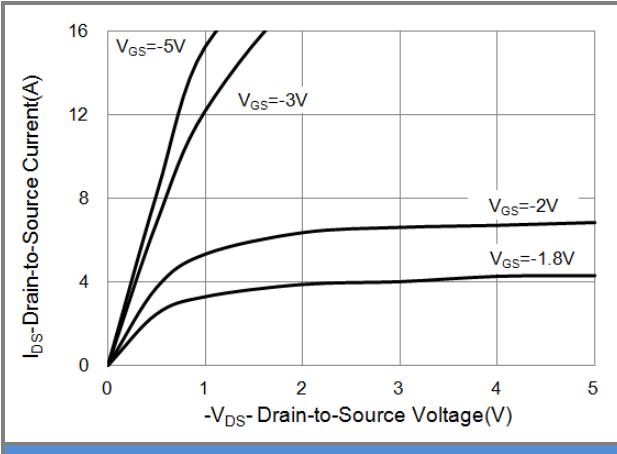


Fig.1 On-Region Characteristics

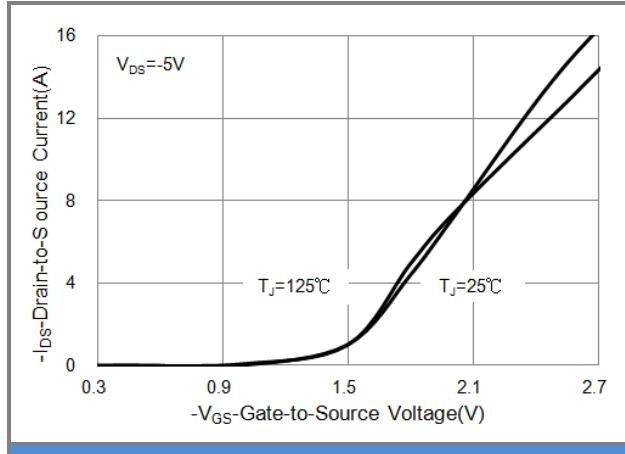


Fig.2 Transfer Characteristics

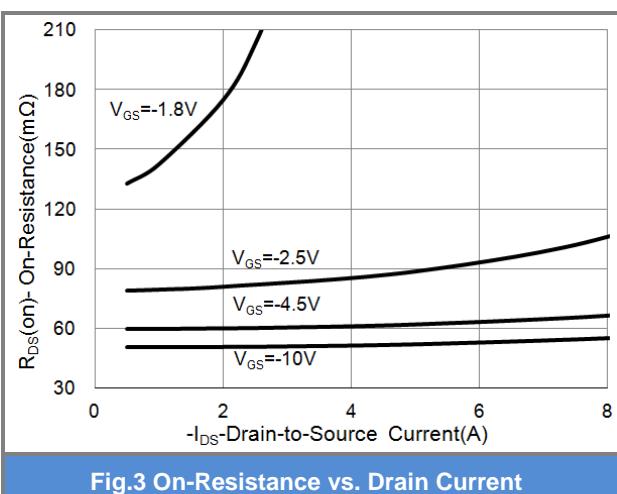


Fig.3 On-Resistance vs. Drain Current

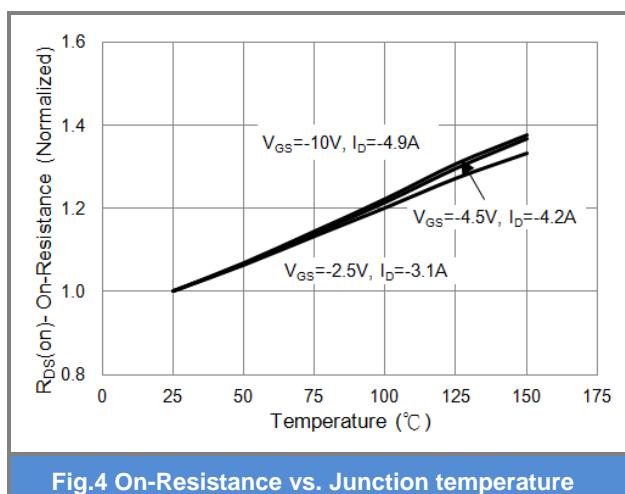


Fig.4 On-Resistance vs. Junction temperature

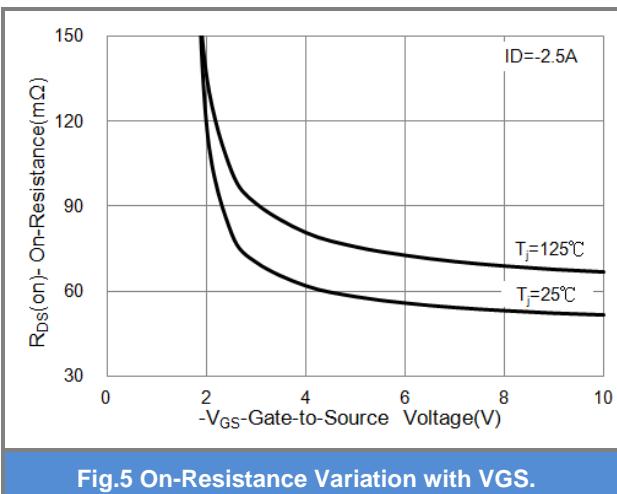


Fig.5 On-Resistance Variation with VGS.

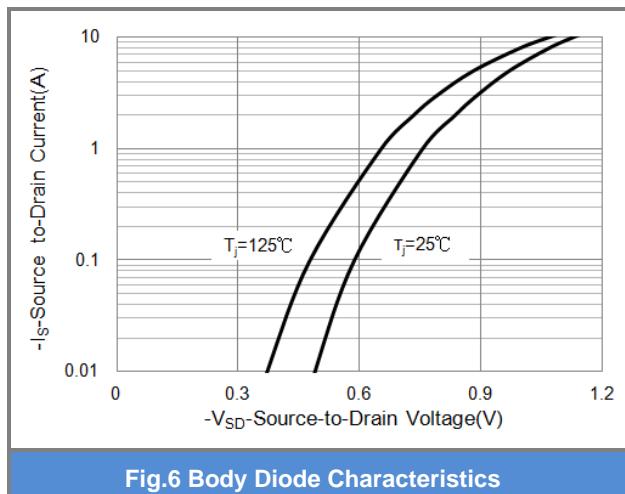


Fig.6 Body Diode Characteristics



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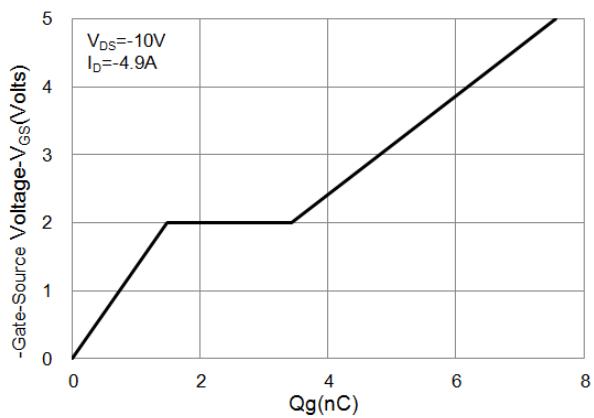


Fig.7 Gate-Charge Characteristics

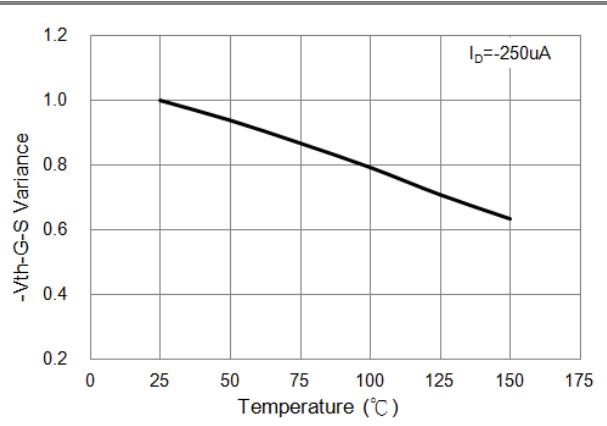


Fig.8 Threshold Voltage Variation with Temperature.

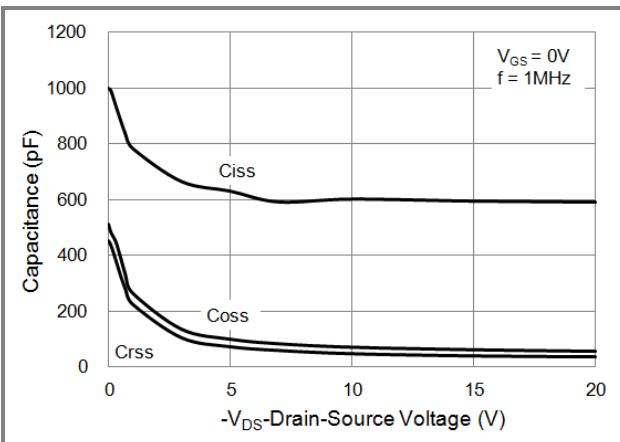


Fig.9 Capacitance vs. Drain-Source Voltage.

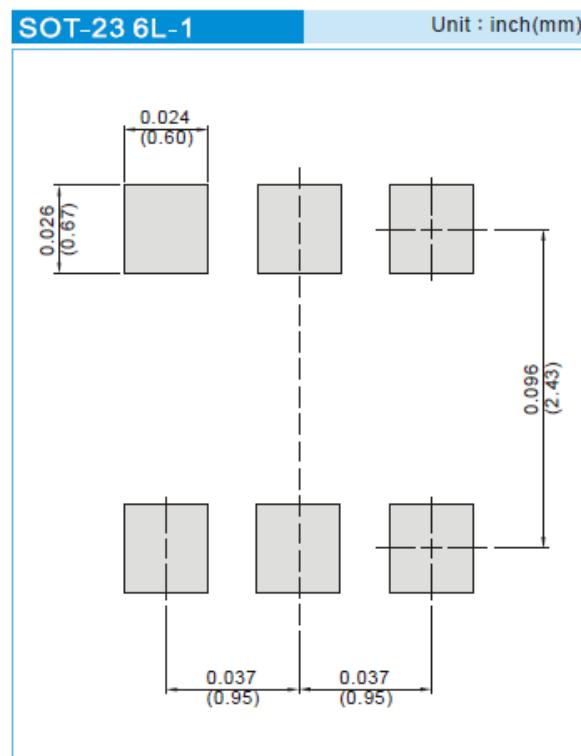


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## PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version
PJS6415AE_S1_00001	SOT-23 6L-1	3K pcs / 7" reel	S5E	Halogen free

## MOUNTING PAD LAYOUT





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